



CRTE110N03L2D-G

General Description:

CRTE110N03L2D-G, the silicon N-channel Enhanced VDMOSFETs, is obtained by advanced Trench Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is SOP8, which accords with the RoHS standard.

Features:

- Fast Switching
- Low ON Resistance
- Low Gate Charge
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test
- Halogen Free

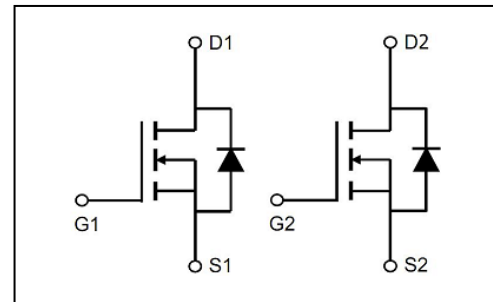
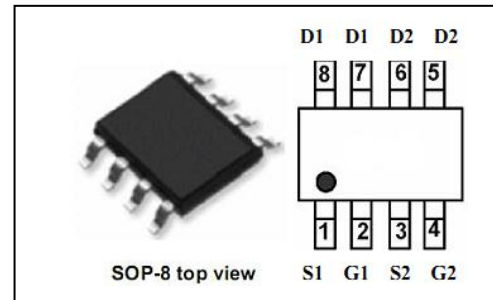
Applications:

Power switch circuit of adaptor and charger.

Absolute ($T_A = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	30	V
I_D	Continuous Drain Current	10	A
	Continuous Drain Current $T_A = 100^\circ\text{C}$	6.4	A
I_{DM}^{a1}	Pulsed Drain Current	40	A
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	93.12	mJ
P_D	Power Dissipation	2	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$

V_{DSS}	30	V
I_D	10	A
$P_D(T_C=25^\circ\text{C})$	2	W
$R_{DS(ON)Typ}$	9.8	$m\Omega$



**Electrical Characteristics** ($T_A = 25^\circ\text{C}$ unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	--	--	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=125^\circ\text{C}$	--	--	100	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V$	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=10A$	--	9.8	11.8	$m\Omega$
	Drain-to-Source On-Resistance	$V_{GS}=4.5V, I_D=8A$	--	12.9	15.5	$m\Omega$
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	--	2.5	V
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	3	--	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=15V, f=1.0MHz$	768	1098	1428	pF
C_{oss}	Output Capacitance		101	202	303	
C_{rss}	Reverse Transfer Capacitance		19	95	171	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$V_{GS}=10V, R_G=6\Omega, V_{DD}=15V, I_D=20A$	--	9.2	--	ns
t_r	Rise Time		--	4.7	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	32.5	--	
t_f	Fall Time		--	6.4	--	
Q_g	Total Gate Charge	$V_{GS}=10V, V_{DD}=15V, I_D=10A$	10	20.2	30	nC
Q_{gs}	Gate to Source Charge		0.66	3.3	5.94	
Q_{gd}	Gate to Drain ("Miller") Charge		0.92	4.6	8.28	
Q_g	Total Gate Charge	$V_{GS}=4.5V, V_{DD}=15V, I_D=10A$	1.9	9.5	17	



Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I _S	Continuous Source Current (Body Diode)		--	--	9.5	A
I _{SM}	Maximum Pulsed Current (Body Diode)		--	--	38	A
V _{SD}	Diode Forward Voltage	I _S =10A, V _{GS} =0V	--	--	1.2	V
trr	Reverse Recovery Time	I _S =20A, T _j = 25 °C dI _F /dt=100A/us,	--	25	--	ns
Qrr	Reverse Recovery Charge		--	12.5	--	nC
I _{RRM}	Reverse Recovery Current		--	1	--	A
Pulse width tp≤300 μs, δ ≤2%						

Symbol	Parameter	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient	62.5	$^{\circ}C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=0.5mH, I_D=19.3A$, Start $T_j=25^{\circ}C$

^{a3}: Recommend soldering temperature defined by IPC/JEDEC J-STD 020

Characteristics Curve:

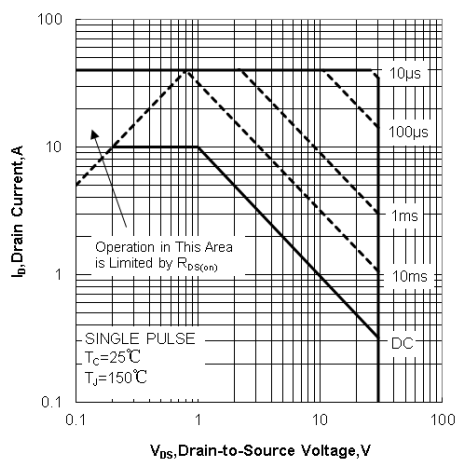


Figure1. Maximum Forward Bias Safe Operating Area

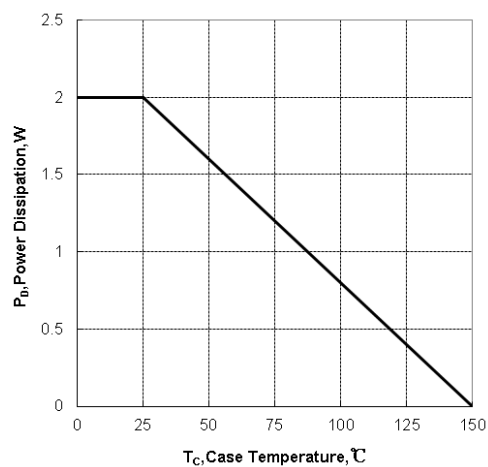


Figure2. Maximum Power Dissipation vs Case Temperature

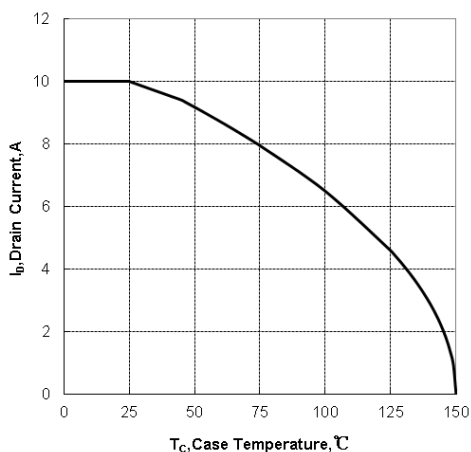


Figure3. Maximum Continuous Drain Current vs Case Temperature

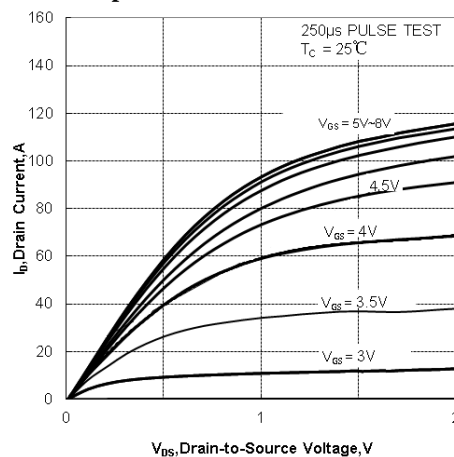


Figure 4. Typical Output Characteristics

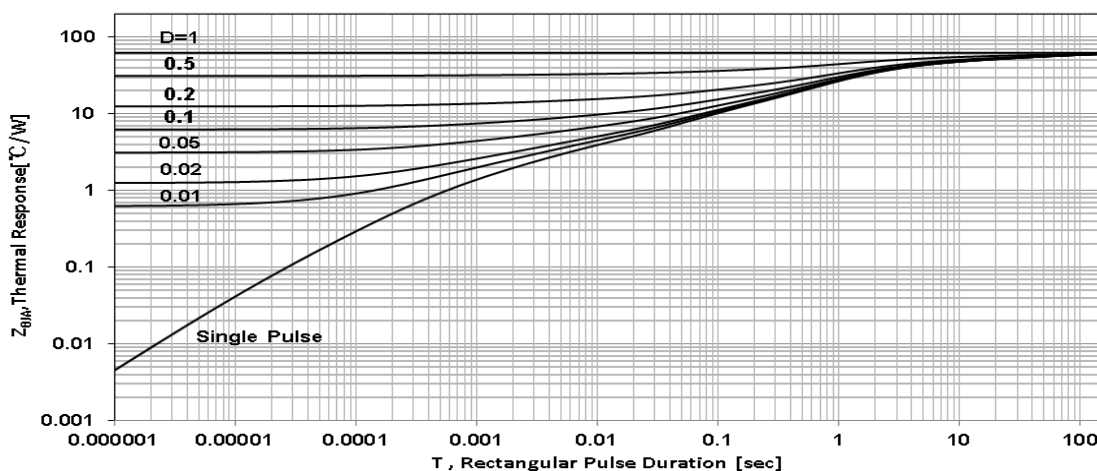
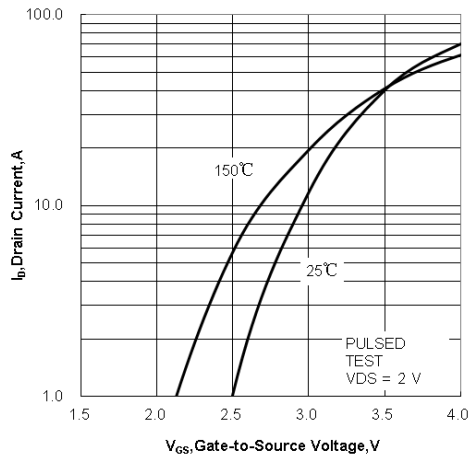
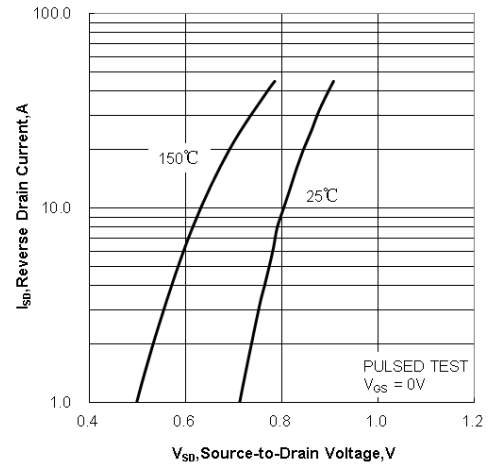
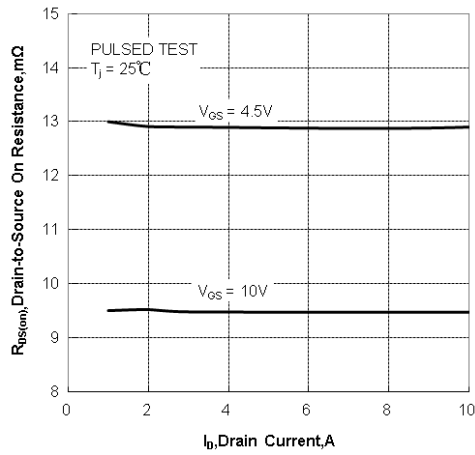
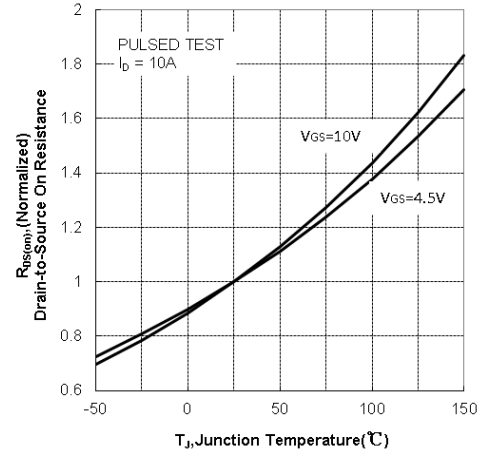
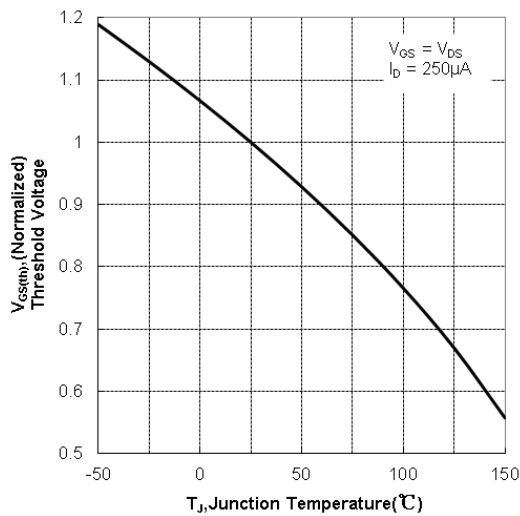
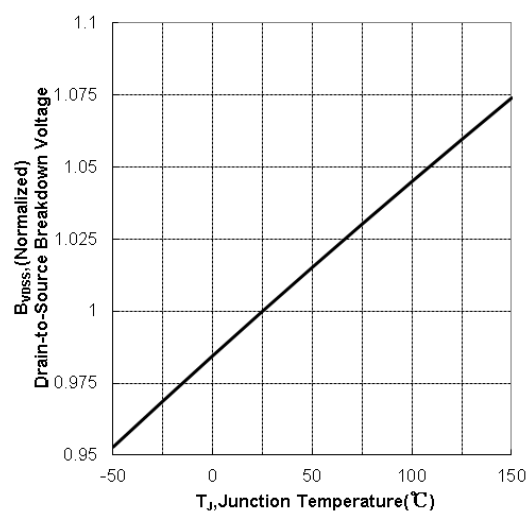


Figure5. Maximum Effective Transient Thermal Impedance, Junction-to- Ambient


Figure 6. Typical Transfer Characteristics

Figure 7. Typical Body Diode Transfer Characteristics

Figure 8. Drain-to-Source On Resistance vs Drain Current

Figure 9. Normalized on Resistance vs Junction Temperature

Figure 10. Normalized Theshold Voltage vs Junction Temperature

Figure 11. Normalized Breakdown Voltage vs Junction Temperature

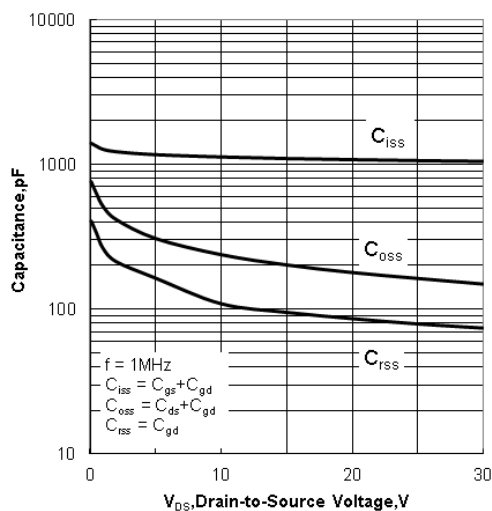


Figure12. Capacitance Characteristics

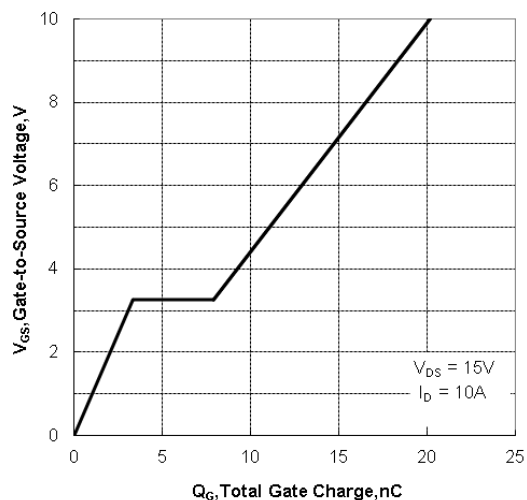


Figure13. Typical Gate Charge vs Gate to Source Voltage

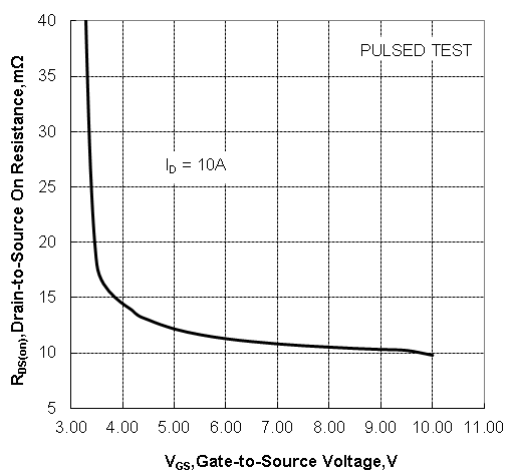


Figure14. Drain-to-Source On Resistance vs Gate Voltage and Drain Current

Test Circuit and Waveform

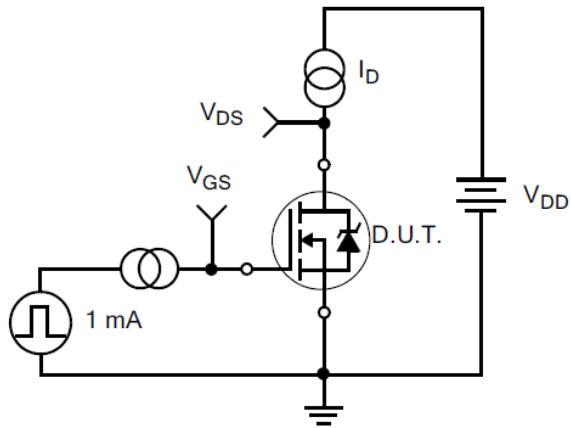


Figure 14. Gate Charge Test Circuit

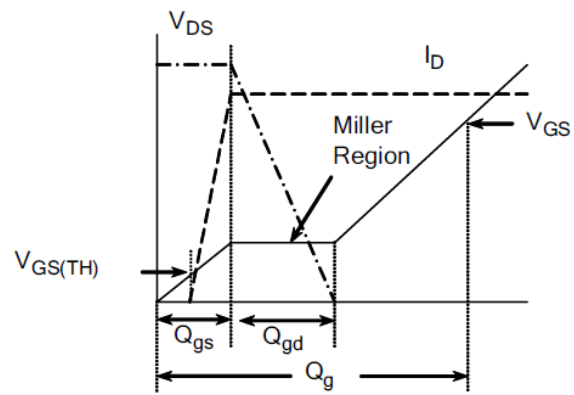


Figure 15. Gate Charge Waveforms

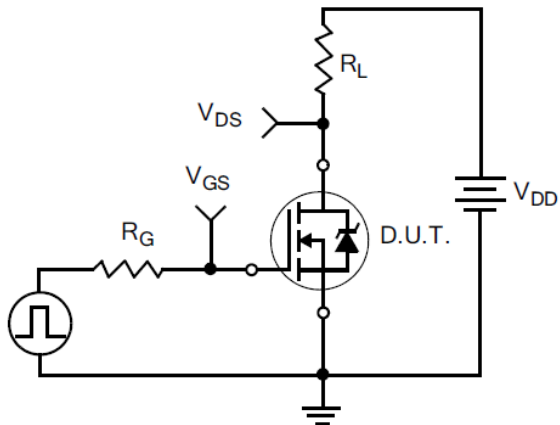


Figure 16. Resistive Switching Test Circuit

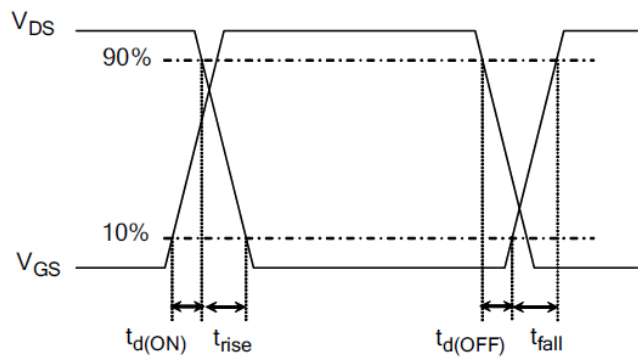


Figure 17. Resistive Switching Waveforms

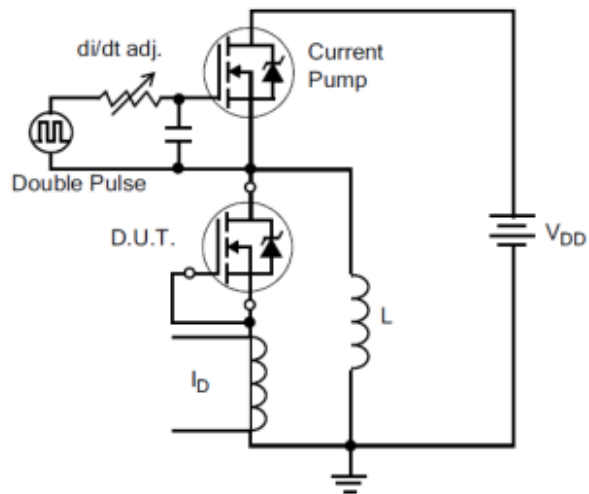


Figure 18. Diode Reverse Recovery Test Circuit

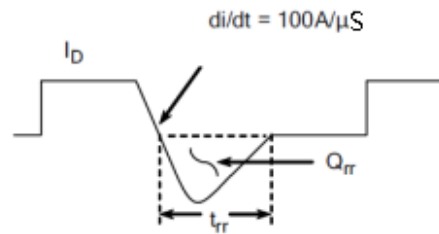


Figure 19. Diode Reverse Recovery Waveform

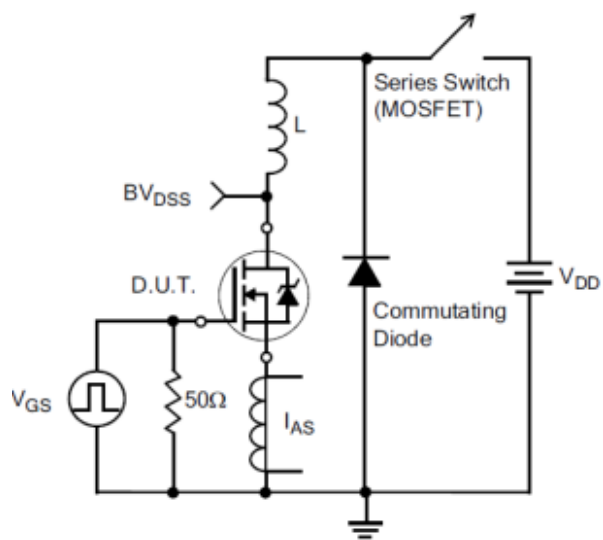


Figure20.Unclamped Inductive Switching Test Circuit

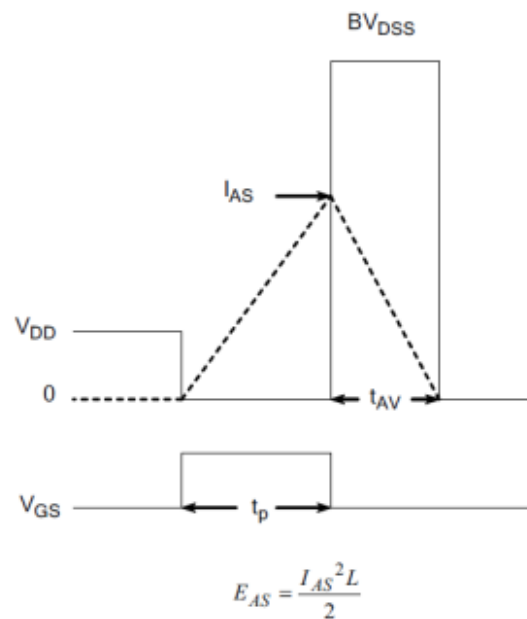
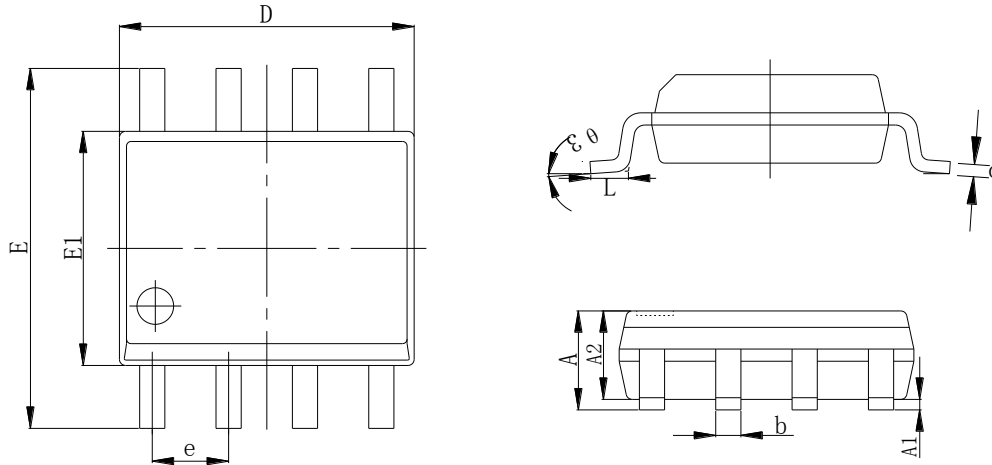


Figure21.Unclamped Inductive Switching Waveform

Package Information:



Items	Values(mm)	
	MIN	MAX
A	1.30	1.80
A1	0.10	0.25
A2	1.30	1.50
E	5.80	6.20
E1	3.80	4.00
D	4.80	5.00
L	0.40	0.90
e	1.27TYP	
b	0.37	0.47
c	0.20 TYP	
θ3	0°	8°

SOP8 Package

**The name and content of poisonous and harmful material in products**

	Hazardous Substance									
	Pb	Hg	Cd	Cr (VI)	PBB	PBDE	DIBP	DEHP	DBP	BBP
Limit	≤0. 1%	≤0. 1%	≤ 0. 01%	≤0. 1%	≤0. 1%	≤0. 1%	≤0. 1%	≤0. 1%	≤0. 1%	≤0. 1%
Lead Frame	○	○	○	○	○	○	○	○	○	○
Molding	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○	○	○	○	○
Solder	×	○	○	○	○	○	○	○	○	○
Note	○: Means the hazardous material is under the criterion of 2011/65/EU. ×: Means the hazardous material exceeds the criterion of 2011/65/EU. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.									

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heatsink, please pay attention to the torsional moment and the smoothness of the heatsink.
3. VDMOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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